

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



FL73282 Half-Bridge Gate Driver

Features

- Floating Channel for Bootstrap Operation to +900 V
- Typically 350 mA / 650 mA Sourcing/Sinking Current Driving Capability for Both Channels
- Common-Mode dv/dt Noise Canceling Circuit
- Extended Allowable Negative V_S Swing to -9.8 V for Signal Propagation at V_{CC}=V_{BS}=15 V
- Vcc & VBs Supply Range from 10 V to 20 V
- UVLO Functions for Both Channels
- Matched Propagation Delay Below 50 ns
- Built-in 170 ns Dead-Time
- Output in Phase with Input Signal

Applications

- Fluorescent Lamp Ballast
- HID Ballast
- SMPS
- Motor Driver
- General Purpose Half Bridge Topology

Description

The FL73282, a monolithic half bridge gate-drive IC, can drive MOSFETs and IGBTs that operate up to +900 V. Fairchild's high-voltage process and common mode noise canceling technique provides stable operation of the high-side driver under high-dV_S/dt noise circumstances. An advanced level-shift circuit allows high-side gate driver operation up to Vs=-9.8 V (typical) for VBs=15 V. The UVLO circuits for both channels prevent malfunction when Vcc or VBs is lower than the specified threshold voltage. Output drivers typically source/sink 350 mA / 650 mA, respectively, which is suitable for all kinds of half- and full-bridge inverters.



Figure 1. SOP 8

Ordering Information

ordering mornidation								
Part Number	Operating Temperature Range	Package	Packing Method					
FL73282MX ⁽¹⁾	-40°C to +125°C	8-Lead, Small Outline Integrated Circuit, (SOIC)	Tape & Reel					

Note:

1. These devices passed wave-soldering test by JESD22A-111.

Typical Application Diagram

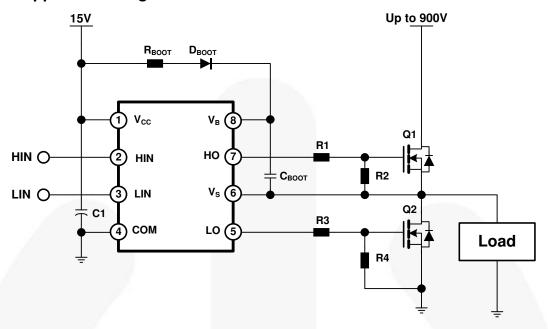


Figure 2. Application Circuit for Half Bridge Topology

Internal Block Diagram

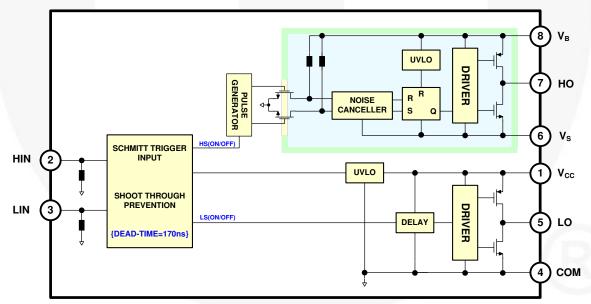


Figure 3. Functional Block Diagram

Pin Configuration

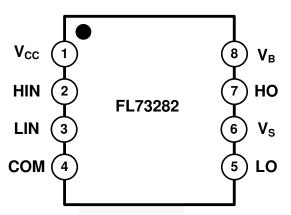


Figure 4. Pin Assignments (Top View)

Pin Definitions

Pin	Name	I/O	Description
1	V _{CC}		Low-Side Supply Voltage
2	HIN	I	Logic Input for High-Side Gate Driver Output
3	LIN	I	Logic Input for Low-Side Gate Driver Output
4	COM		Logic Ground and Low-Side Driver Return
5	LO	0	Low-Side Driver Output
6	Vs	I	High-Voltage Floating Supply Return
7	НО	0	High-Side Driver Output
8	V _B	I	High-Side Floating Supply

Absolute Maximum Ratings

Stresses exceeding the Absolute Maximum Ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit
Vs	High-Side Floating Offset Voltage	V _B -24	V _B +0.3	V
V _B	High-Side Floating Supply Voltage	-0.3	924.0	V
V _{CC}	Low-Side and Logic-Fixed Supply Voltage	-0.3	24	V
V _{HO}	High-Side Floating Output Voltage V _{HO}	V _S -0.3	V _B +0.3	V
V_{LO}	Low-Side Floating Output Voltage V _{LO}	-0.3	V _{CC} +0.3	V
V _{IN}	Logic Input Voltage (HIN, LIN)	-0.3	V _{CC} +0.3	V
COM	Logic Ground	V _{CC} -24	V _{CC} +0.3	V
dV _S /dt	Allowable Offset Voltage Slew Rate	1/	±50	V/ns
P _D ⁽³⁾⁽⁴⁾⁽⁵⁾	Power Dissipation		0.625	W
θ_{JA}	Thermal Resistance		200	°C/W
TJ	Junction Temperature		150	°C
T _{STG}	Storage Temperature	-55	150	°C

Notes:

- 2. Mounted on 76.2 x 114.3 x 1.6 mm PCB (FR-4 glass epoxy material).
- 3. Refer to the following standards: JESD51-2: Integral circuit's thermal test method environmental conditions, natural convection; JESD51-3: Low effective thermal conductivity test board for leaded surface-mount packages.
- 4. Do not exceed maximum power dissipation (P_D) under any circumstances.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
V _B	High-Side Floating Supply Voltage	V _S +10	V _S +20	V
Vs	High-Side Floating Supply Offset Voltage	6-V _{CC}	900	V
V _{HO}	High-Side (HO) Output Voltage	Vs	V_B	V
V _{LO}	Low-Side (LO) Output Voltage	COM	Vcc	V
V _{IN}	Logic Input Voltage (HIN, LIN)	COM	V _{CC}	V
Vcc	Low-Side Supply Voltage	10	20	V
T _A	Ambient Temperature	-40	+125	°C

Static Electrical Characteristics

 $V_{BIAS}(V_{CC},\,V_{BS})$ = 15.0 V, T_A = 25°C, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to V_S and COM and are applicable to the respective outputs HO and LO.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit	
Power Su	Power Supply Section						
I _{QCC}	Quiescent V _{CC} Supply Current	V _{IN} =0 V or 5 V		80	180	μА	
I _{QBS}	Quiescent V _{BS} Supply Current	V _{IN} =0 V or 5 V		50	120	μА	
IPCC	Operating V _{CC} Supply Current	f _{IN} =20 kHz, rms value			550	μА	
IPBS	Operating V _{BS} Supply Current	f _{IN} =20 kHz, rms value			600	μА	
I _{LK}	Offset Supply Leakage Current	V _B =V _S =900 V			10	μА	
Bootstrap	pped Supply Section						
V _{CCUV+} V _{BSUV+}	V _{CC} & V _{BS} Supply Under-Voltage Positive going Threshold		8.2	9.2	10.0	٧	
V _{CCUV} - V _{BSUV} -	V_{CC} & V_{BS} Supply Under-Voltage Negative going Threshold		7.6	8.7	9.6	V	
V _{CCUVH} V _{BSUVH}	V _{CC} Supply Under-Voltage Lockout Hysteresis			0.5		٧	
Input Sec	tion						
V_{IH}	Logic "1" Input Voltage		2.5			V	
V_{IL}	Logic "0" Input Voltage				0.8	V	
$I_{\text{IN+}}$	Logic "1" Input Bias Current	V _{IN} =5 V		20	50	μА	
I _{IN-}	Logic "0" Input Bias Current	V _{IN} =0 V		1.0	2.0	μА	
R _{IN}	Logic Input Pull-Down Resistance		100	250		ΚΩ	
Gate Driv	er Output Section						
V _{OH}	High-Level Output Voltage, V_{BIAS} - V_{O}	I _O =0 A			85	mV	
V_{OL}	Low-Level Output Voltage, Vo	I _O =0 A			85	mV	
I _{O+}	Output HIGH Short-Circuit Pulsed Current	V _O =0 V,V _{IN} =5 V with PW≤10 μs	250	350		mA	
I _{O-}	Output LOW Short-Circuit Pulsed Current	V _O =15 V,V _{IN} =0 V with PW≤10 μs	500	650		mA	
Vs	Allowable Negative V_{S} Pin Voltage for HIN Signal Propagation to HO			-9.8	-7.0	V	

Dynamic Electrical Characteristics

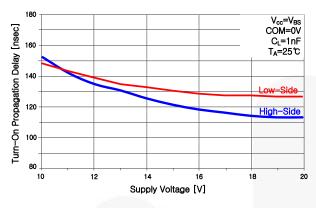
 $V_{BIAS}(V_{CC}, V_{BS}) = 15.0 \text{ V}, V_S = COM, C_L = 1000 \text{ pF} \text{ and } T_A = 25^{\circ}\text{C}, \text{ unless otherwise specified.}$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ton	Turn-On Propagation Delay	V _S =0 V	80	150	220	ns
toff	Turn-Off Propagation Delay	Vs=0 V or 900 V ⁽⁵⁾	80	150	220	ns
t _R	Turn-On Rise Time	V _{LIN} =V _{HIN} =5 V		60	140	ns
t _F	Turn-Off Fall Time	V _{LIN} =V _{HIN} =0 V		30	80	ns
DT	Dead Time		70	170	270	ns
MT	Delay Matching, HS & LS Turn-on/off				50	ns
t _{PW}	Minimum Input Pulse Width that changes the Output ⁽⁵⁾⁽⁶⁾				220	ns

Notes:

- These parameters are guaranteed by design.
 The minimum input pulse width time included dead time

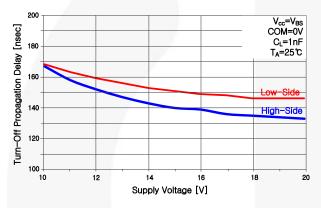
Typical Characteristics



300 V_{cc}=V_{BS}=15V COM=0V 275 C_L=1nF 250 Delay 225 200 Propagation 175 Low-150 125 Turn-On 100 75 40 120 Temperature [℃]

Figure 5. Turn-On Propagation Delay vs. Supply Voltage

Figure 6. Turn-On Propagation Delay vs. Temperature



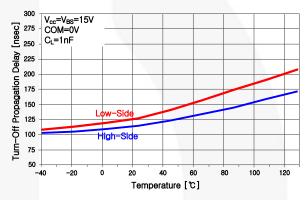
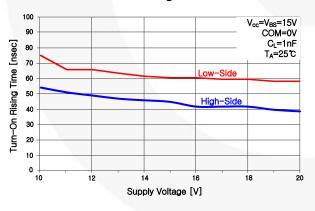


Figure 7. Turn-Off Propagation Delay vs. Supply Voltage

Figure 8. Turn-Off Propagation Delay vs. Temperature



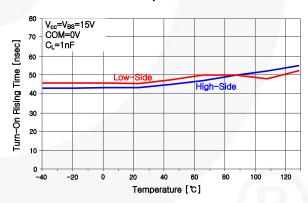


Figure 9. Turn-On Rising Time vs. Supply Voltage

Figure 10. Turn-On Rising Time vs. Temperature

Typical Characteristics (Continued) | Solution | Continued | Cont

10

12

V_{cc}=V_{BS} COM=0V C_L=1nF T_A=25℃

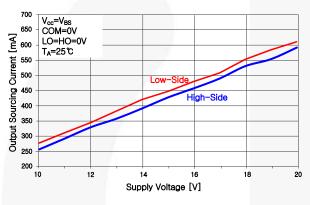
Figure 11. Turn-Off Falling Time vs. Supply Voltage

Supply Voltage [V]

16

18

Figure 12. Turn-Off Falling vs. Temperature



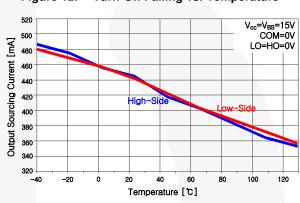
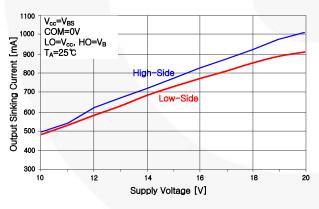


Figure 13. Output Sourcing Current vs. Supply Voltage

Figure 14. Output Sourcing Current vs. Temperature



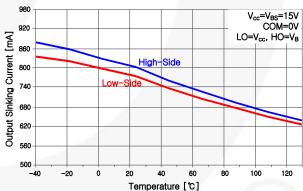
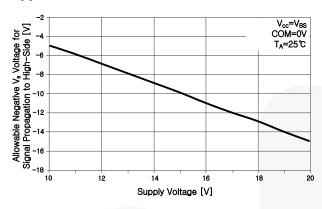


Figure 15. Output Sinking Current vs. Supply Voltage

Figure 16. Output Sinking Current vs. Temperature

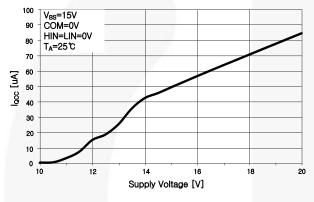
Typical Characteristics (Continued)



Notative Not

Figure 17. Allowable Negative V_S Voltage for Signal Propagation to High Side vs. Supply Voltage

Figure 18. Allowable Negative V_S Voltage for Signal Propagation to High Side vs. Temperature



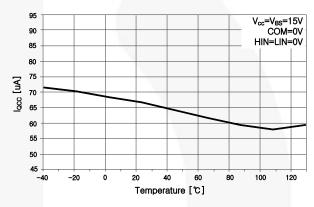
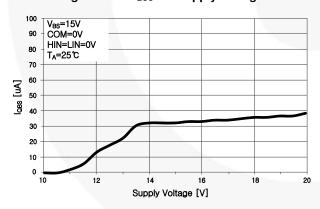


Figure 19. IQCC vs. Supply Voltage

Figure 20. IQCC vs. Temperature



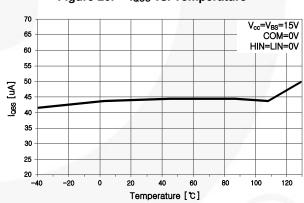


Figure 21. IQBS vs. Supply Voltage

Figure 22. I_{QBS} vs. Temperature

Typical Characteristics (Continued) 0.7 V_{cc}=V_{BS} COM=0V V_{cc}=V_{BS}=15V COM=0V 60 0.6 HIN=LIN=5V HIN=LIN=5V I_L=20mA IL=0A 50 0.5 T_A=25℃ 40 <u>_</u> Ξ 30 Low-Side ₹ 0.3 ٩ 20 High-Side High-Side 0.1 0 Low 0.0 -10 120 -20 60 80 40 Supply Voltage [V] Temperature [℃] Figure 23. High-Level Output Voltage Figure 24. **High-Level Output Voltage** vs. Supply Voltage vs. Temperature 0.26 V_{cc}=V_{BS} COM=0V HIN=LIN=0V V_{cc}=V_{BS}=15V COM=0V 0.24 60 HIN=LIN=0V 0.22 I_L=20mA IL=0A 50 T_A=25℃ 40 0.18 <u>_</u> Ξ 30 호 _{0.14} ⋄ 20 High-Side 0.12 0.10 High-\$ide 0 0.08 Low 0.06 -10 10 12 16 40 60 Supply Voltage [V] Temperature [℃] Figure 25. **Low-Level Output Voltage** Figure 26. **Low-Level Output Voltage** vs. Temperature vs. Supply Voltage 100 40 V_{cc}=V_{BS} COM=0V HIN=LIN=5V 90 IN=V_{CC} or IN=0V 80 T_A=25℃ 30 70 IN+/IN- [uA] 60 50 20 HIN ŧ 40 30 10 20

Figure 27. Input Bias Current vs. Supply Voltage

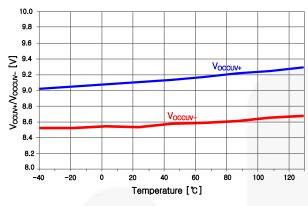
10 Supply Voltage [V]

Figure 28. Input Bias Current vs. Temperature

Temperature [℃]

٥

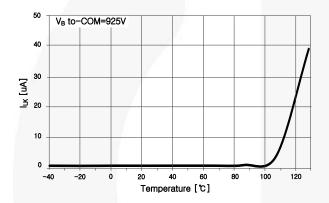
Typical Characteristics (Continued)



9.8 9.6 9.4 9.0 9.0 8.8 8.6 8.2 8.0 7.8 -40 -20 0 20 40 60 80 100 120 Temperature [°C]

Figure 29. V_{CC} UVLO Threshold Voltage vs. Temperature

Figure 30. V_{BS} UVLO Threshold Voltage vs. Temperature



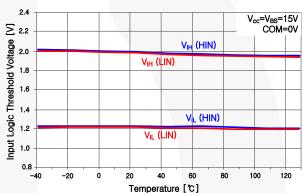


Figure 31. V_B to COM Leakage Current vs. Temperature

Figure 32. Input Logic Threshold Voltage vs. Temperature

Switching Time Definitions

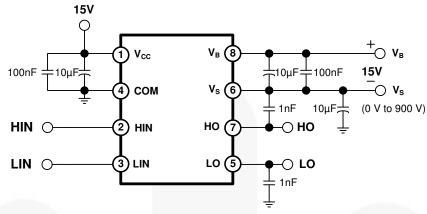


Figure 33. Switching Time Test Circuit

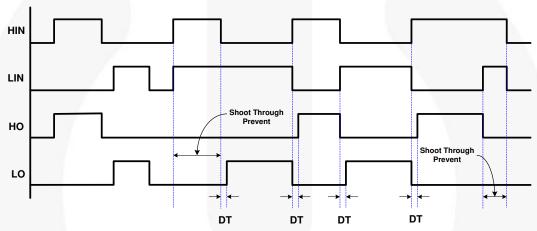
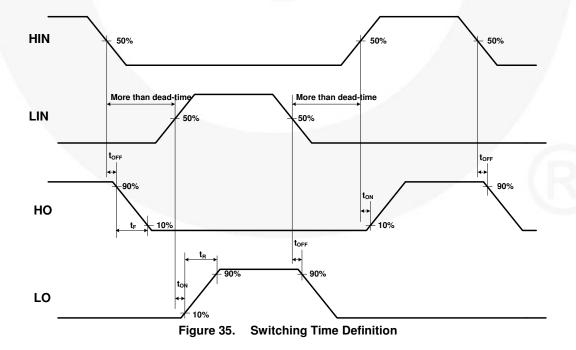


Figure 34. Input / Output Timing Diagram



Switching Time Definitions (Continued)

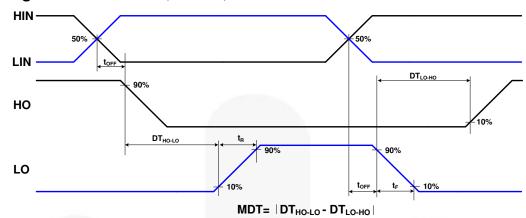
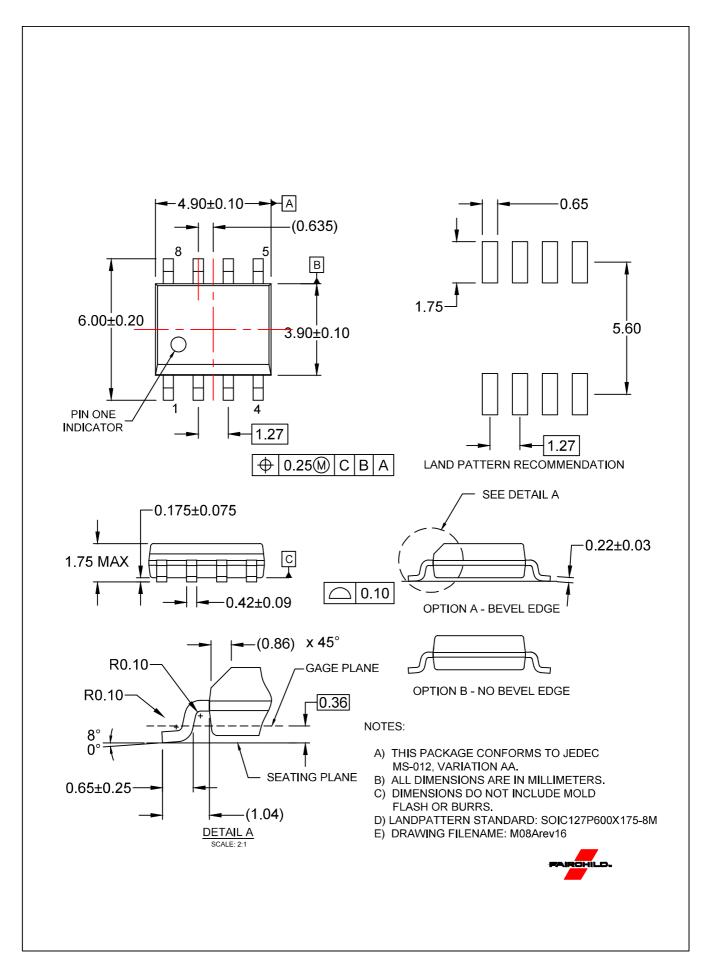


Figure 36. Internal Dead Time Definition



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Phone: 421 33 790 2910 **Japan Customer Focus Center**Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative